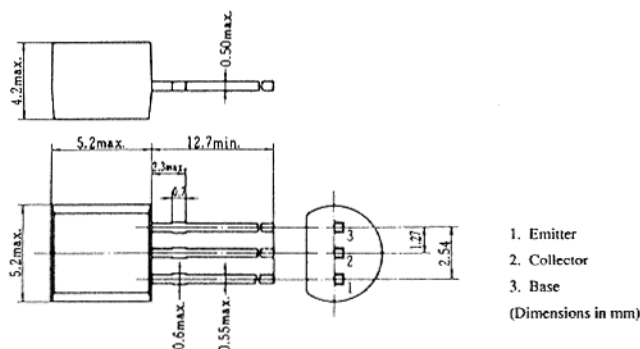


2SA673, 2SA673A

SILICON PNP EPITAXIAL

LOW FREQUENCY AMPLIFIER

Complementary pair with 2SC1213 and 2SC1213A

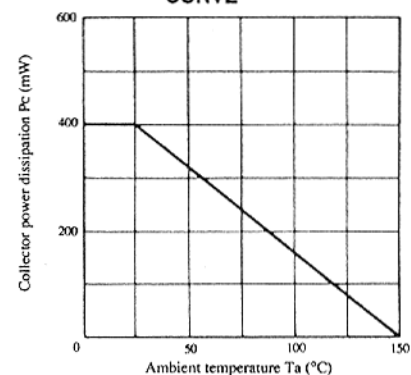


(JEDEC TO-92)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SA673	2SA673A	Unit
Collector to base voltage	V _{CB0}	-35	-50	V
Collector to emitter voltage	V _{CEO}	-35	-50	V
Emitter to base voltage	V _{EB0}	-4	-4	V
Collector current	I _C	-500	-500	mA
Collector power dissipation	P _C	400	400	mW
Junction temperature	T _j	150	150	°C
Storage temperature	T _{stg}	-55 to +150	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	2SA673			2SA673A			Unit
			min.	typ.	max.	min.	typ.	max.	
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -10μA, I _E = 0	-35	—	—	-50	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, R _{BE} = ∞	-35	—	—	-50	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C = 0	-4	—	—	-4	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -20V, I _E = 0	—	—	-0.5	—	—	-0.5	μA
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = -150mA, I _B = -15mA**	—	-0.2	-0.6	—	-0.2	-0.6	V
DC current transfer ratio	h _{FE} *	V _{CE} = -3V, I _C = -10mA	60	—	320	60	—	320	
DC current transfer ratio	h _{FE}	V _{CE} = -3V, I _C = -500mA**	10	—	—	10	—	—	
Base to emitter voltage	V _{BE}	V _{CE} = -3V, I _C = -10mA	—	-0.64	—	—	-0.64	—	V

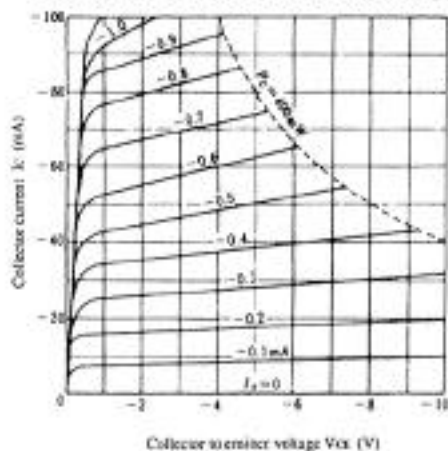
* The 2SA673 and 2SA673A are grouped by h_{FE} as follows.

** Pulse Test

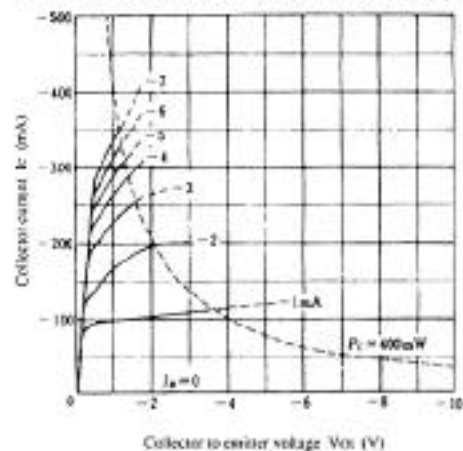
B	C	D
60 to 120	100 to 200	160 to 320

2SA673, 2SA673A

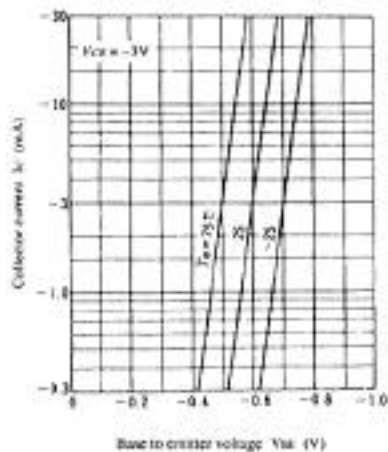
TYPICAL OUTPUT CHARACTERISTICS (1)



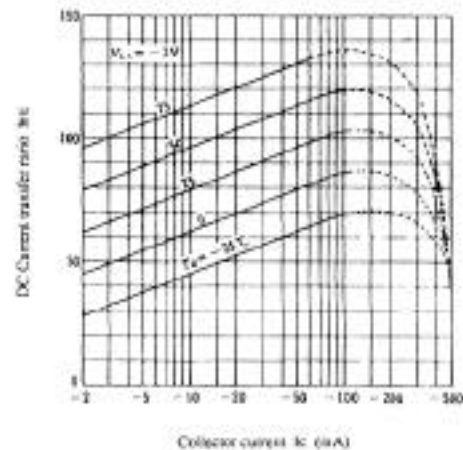
TYPICAL OUTPUT CHARACTERISTICS (2)



TYPICAL TRANSFER CHARACTERISTICS



DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT VS. COLLECTOR CURRENT

